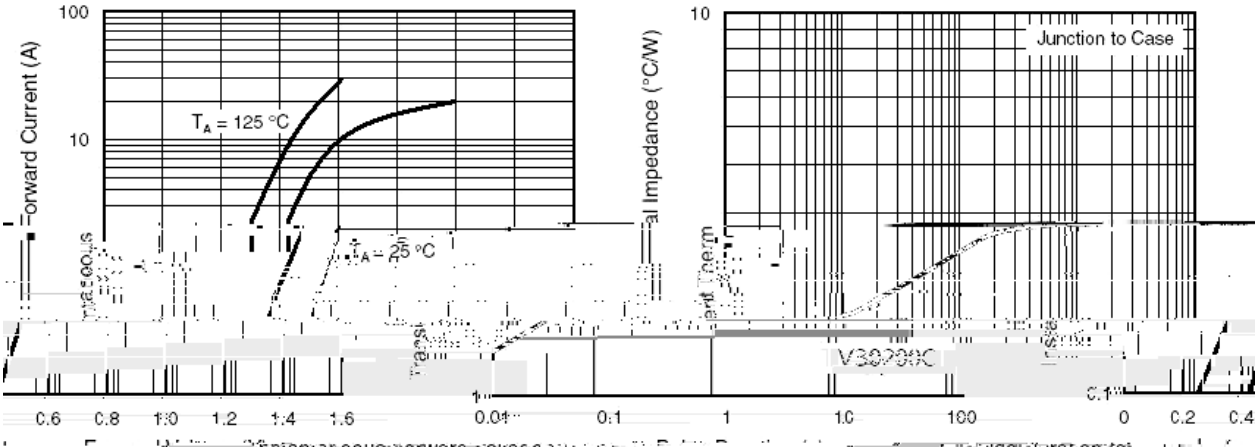
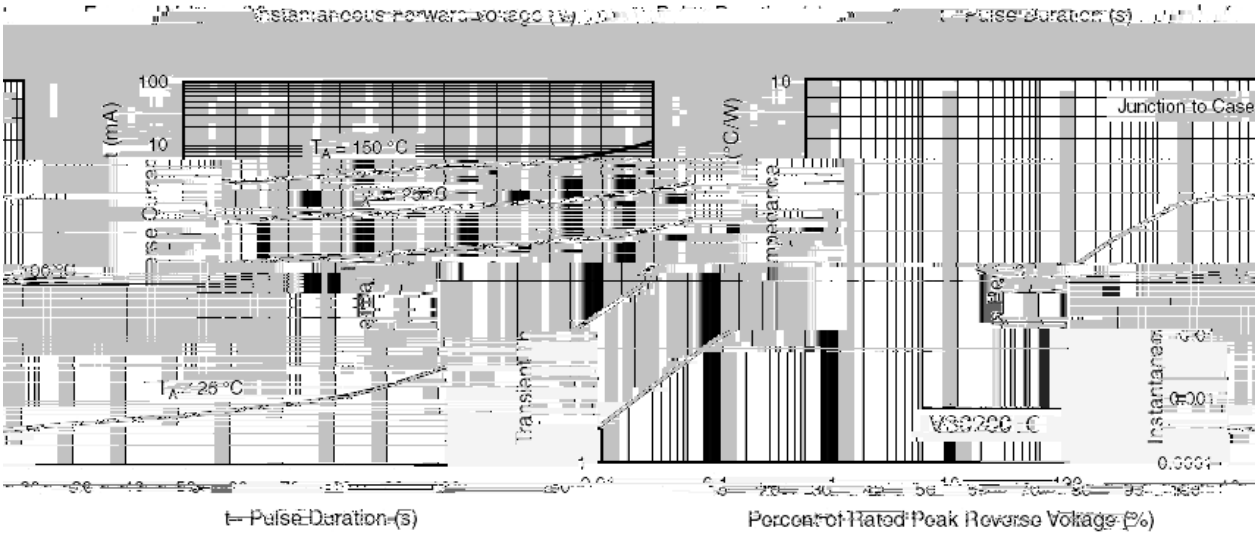
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RSM} V_{DC}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
Average Rectified Forward Current	$I_{F(AV)}$	2×15	A
Non Repetitive Peak Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Case	R_{Jc}	4.6	/W
Junction and Storage Temperature Range	T_j T_{stg}	-40 +150	

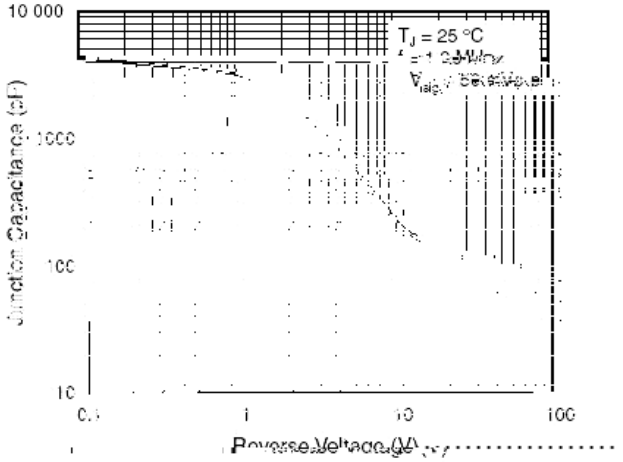
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Reverse Voltage	V_{BR}	I_R=1mA(Ta=25)	200			V
Forward Voltage	V_F	I_F =5A(Ta=25)		0.73	0.85	V
		I_F =10A(Ta=25)		0.80	0.95	V
		I_F =15A(Ta=25)		0.92	1.15	V
		I_F =5A(Ta=125)		0.58		V
		I_F =10A(Ta=125)		0.66		V
		I_F =15A(Ta=125)		0.71	0.85	V
Instantaneous Reverse Current	I_R Note 1	V_R=200V(Ta=25)		4	20	A
		V_R=200V(Ta=125)		5	10	mA

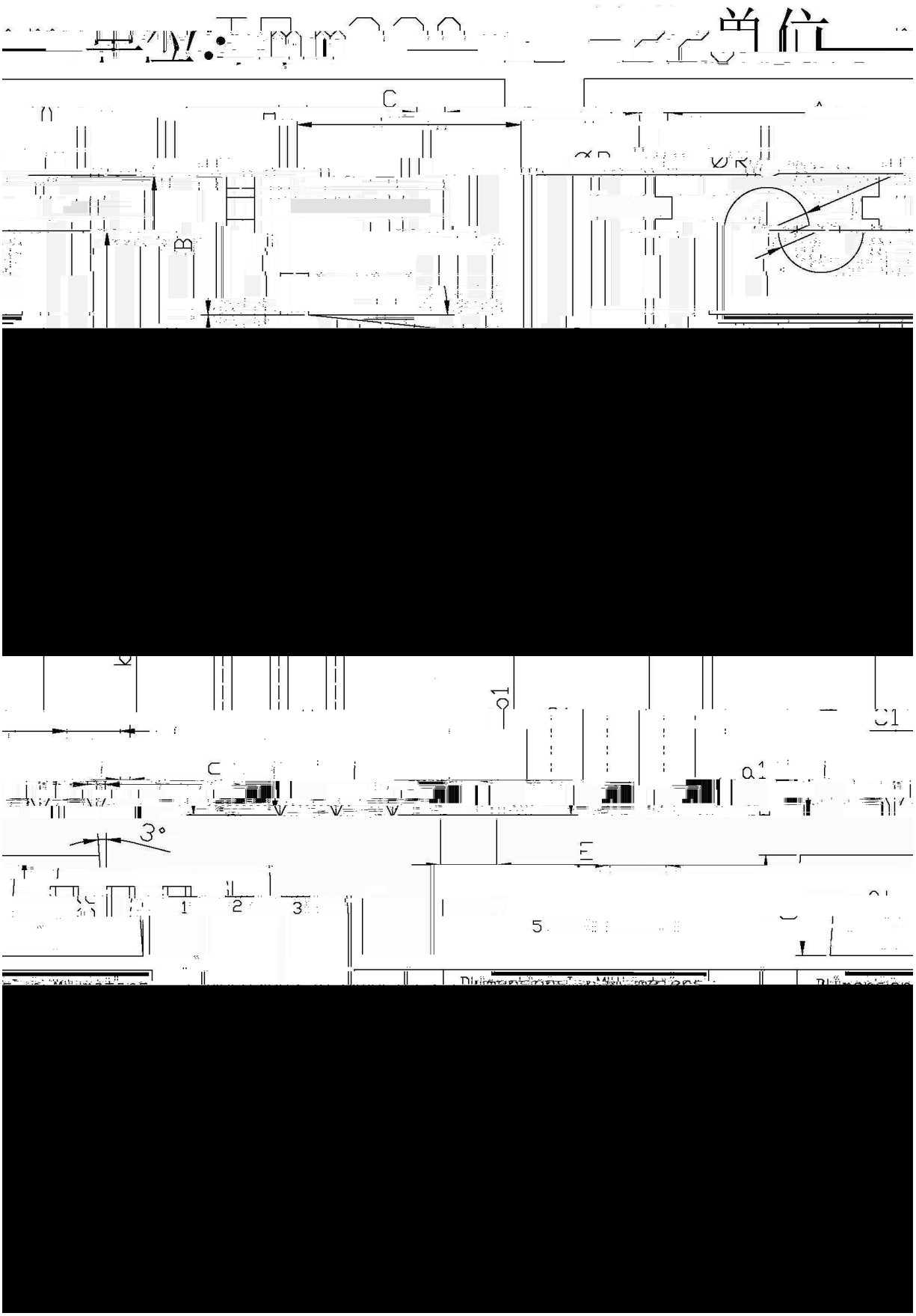
/Notes

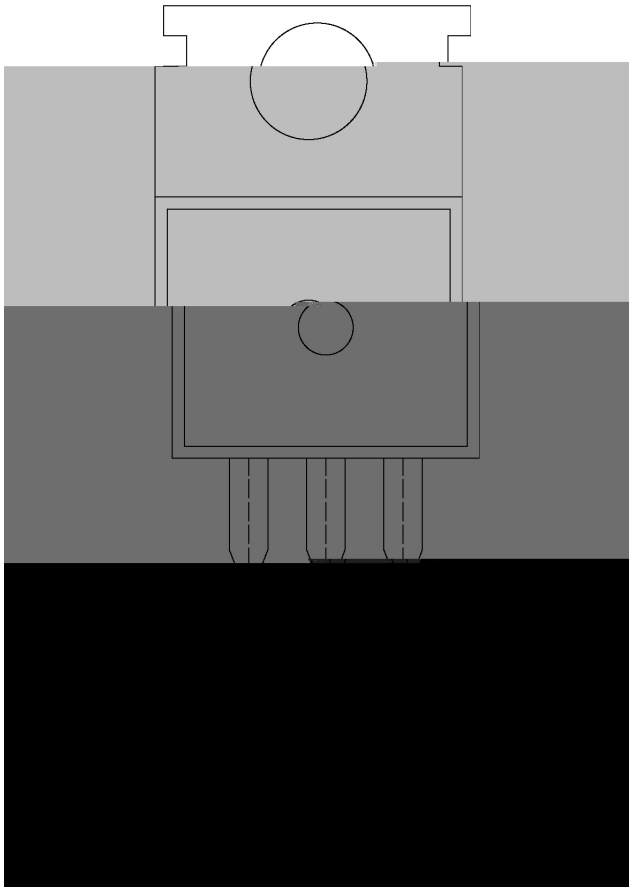
1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip

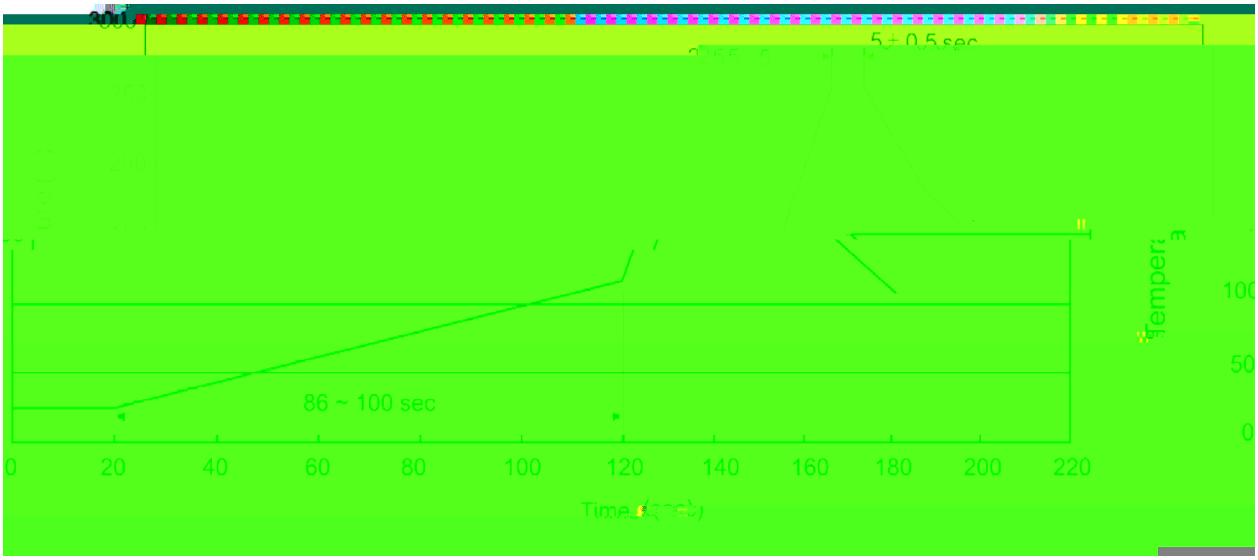

100
10
Forward Current (A)
T_A = 125 °C
T_A = 25 °C
0.6
0.8
1.0
1.2
1.4
1.6
Junction to Case
0.01
0.1
1
10
100
0
0.2
0.4
Pulse Duration (s)


100
10
(mA)
T_A = 150 °C
T_A = 25 °C
Junction to Case
t – Pulse Duration (s)
Percent of Rated Peak Reverse Voltage (%)


10 000
1000
100
10
T_J = 25 °C
0.1
1
10
100
Reverse Voltage (V)







					Note:
1	25	150	60	90sec;	1.Preheating:25~150